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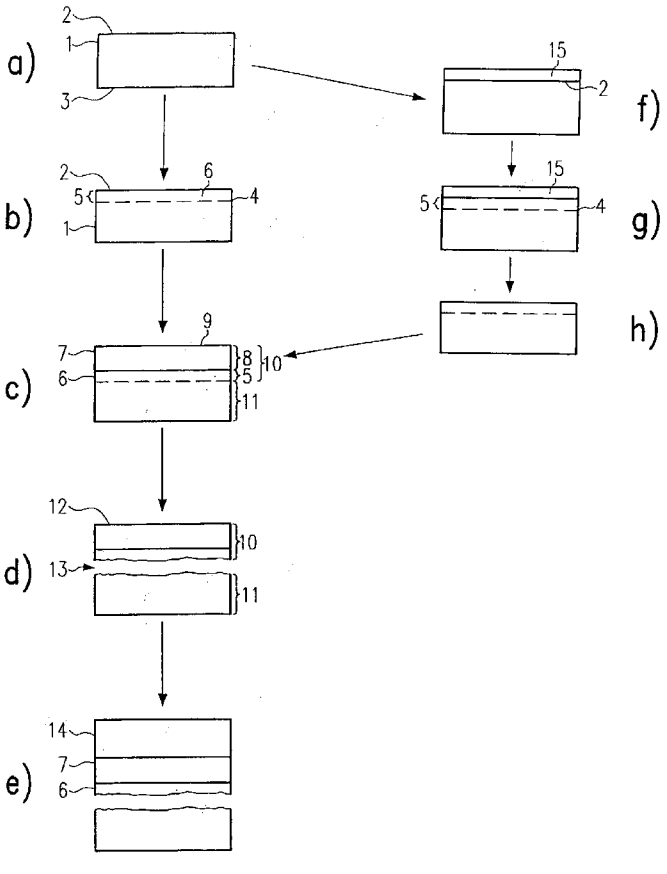
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(54) Title: A METHOD OF PREPARATION OF AN EPITAXIAL SUBSTRATE



(57) Abstract: The invention relates to a method of preparation of an epitaxial substrate, in particular a GaN, a SiGe, AlN or InN epitaxial substrate. It is the object of the present invention to provide a process of preparation of an epitaxial substrate which further reduces the influence of the substrate while being at the same time economically viable. The object is solved by providing a base substrate, implanting atomic species in the base substrate to create a weak layer like zone, providing an epitaxial stiffening layer on a surface of a base substrate at a first temperature and isolating the stiffening layer at a second higher temperature, in particular together with a sub-layer of the base substrate, from the remainder of the base substrate, whereby the isolated material creates a pseudo substrate on which a homo- or heteroepitaxial layer is provided.

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